Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

- 1. (Currently amended) A light emitting diode, comprising:
 - a semiconductor substrate;
- a light-emitting region including an active layer provided between a first conductivity type cladding layer formed over the semiconductor substrate and a second conductivity type cladding layer;
- a transparent conductive film made of a metal oxide and located over the lightemitting region;
 - a first electrode formed on the upper side of the transparent conductive film;
- a second electrode formed on the whole or a part of the bottom of the semiconductor substrate;
- a layer for preventing exfoliation of the transparent conductive film, the preventing layer being made of a compound semiconductor containing at least aluminum and located between the light-emitting region second conductivity type cladding layer and the transparent conductive film, the preventing layer having a high carrier concentration; [[and]]

an undoped layer or a low carrier concentration layer formed between the active layer and the second conductivity type cladding layer, wherein the undoped layer or the low carrier concentration layer is a layer other than the active layer and comprises a bandgap greater than the active layer;

a second conductivity type contact layer formed between the second conductivity type cladding layer and the preventing layer; and

an undoped layer inserted into the second conductivity type contact layer.

- 2. (Original) The light emitting diode as defined in claim 1, wherein:
- the preventing layer contains a conductivity type determination impurity at a concentration of 1×10^{19} cm⁻³ or higher.
- 3. (Original) The light emitting diode as defined in claim 1, wherein: the preventing layer has a film thickness of 300 nm or less.

- 4. (Original) The light emitting diode as defined in claim 2, wherein: the preventing layer has a film thickness of 300 nm or less.
- 5. (Original) The light emitting diode as defined in claim 1, wherein: the transparent conductive film is made of indium tin oxide.
- 6. (Original) The light emitting diode as defined in claim 2, wherein: the transparent conductive film is made of indium tin oxide.
- 7. (Original) The light emitting diode as defined in claim 1, wherein: the preventing layer is made of an arsenic compound.
- 8. (Original) The light emitting diode as defined in claim 2, wherein: the preventing layer is made of an arsenic compound.
- 9. (Original) The light emitting diode as defined in claim 1, wherein: the light-emitting region is made of $(Al_XGa_{1-X})_YIn_{1-Y}P$ $(0 \le X \le 1, 0 \le Y \le 1)$.
- 10. (Original) The light emitting diode as defined in claim 2, wherein: the light-emitting region is made of $(Al_XGa_{1-X})_YIn_{1-Y}P$ $(0 \le X \le 1, 0 \le Y \le 1)$.
- 11. (Original) The light emitting diode as defined in claim 1, wherein: the preventing layer is an AlGaAs layer having a bandgap which is smaller than that of the active layer; and the AlGaAs layer is made of $Al_XGa_{1-X}As$ (0.01 $\leq X \leq$ 0.43).
- 12. (Previously presented) The light emitting diode as defined in claim 1, wherein: the preventing layer has a carrier concentration of 1×10^{19} cm⁻³ or higher.
- 13. (Original) The light emitting diode as defined in claim 11, wherein:
 the AlGaAs layer has a carrier concentration of 1 x 10¹⁹ cm⁻³ or higher.
- 14. (Previously presented) The light emitting diode as defined in claim 1, wherein: the preventing layer is added with at least one of Zn, Be, and Mg.

- 15. (Original) The light emitting diode as defined in claim 11, wherein: the AlGaAs layer is added with at least one of Zn, Be, and Mg.
- 16. (Previously presented) The light emitting diode as defined in claim 1, wherein: the preventing layer is added with at least one of Zn, Be and Mg, and C; and C is autodoped.
- 17. (Original) The light emitting diode as defined in claim 11, wherein: the AlGaAs layer is added with at least one of Zn, Be and Mg, and C; and C is autodoped.
- 18. (Previously presented) The light emitting diode as defined in claim 1, wherein: the preventing layer is formed at a growth temperature of 600°C or lower.
- 19. (Original) The light emitting diode as defined in claim 11, wherein: the AlGaAs layer is formed at a growth temperature of 600°C or lower.
- 20. (Previously presented) The light emitting diode as defined in claim 1, wherein: the preventing layer is formed at a V/III ratio in raw materials of 50 or less at the time of growth.
- 21. (Original) The light emitting diode as defined in claim 11, wherein: the AlGaAs layer is formed at a V/III ratio in raw materials of 50 or less at the time of growth.
- 22. (Original) The light emitting diode as defined in claim 11, wherein: the transparent conductive film is made of indium tin oxide.
- 23. (Original) The light emitting diode as defined in claim 11, wherein: the light-emitting region is made of $(Al_XGa_{1-X})_YIn_{1-Y}P$ $(0 \le X \le 1, 0 \le Y \le 1)$.